CHENMKO ENTERPRISE CO.,LTD

SURFACE MOUNT

SCHOTTKY BARRIER DIODE

VOLTAGE 40 Volts CURRENT 0.02 Ampere

CH402H-40PT

Lead free devices

APPLICATION

* Low barrier diode for detectors up to GHz frequencies

FEATURE

* Small surface mounting type. (SOT-143)
* Extremely low forward voltage.
* A composite component and is ideal for reducing the number of components used.
* High reliability

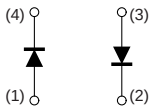
CONSTRUCTION

* Silicon epitaxial planar

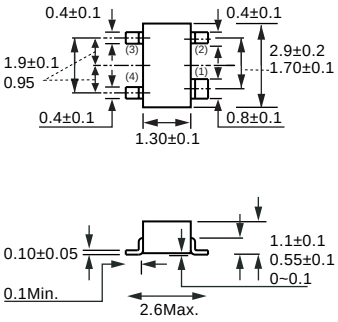
MARKING

* H1

CIRCUIT



SOT-143



Dimensions in millimeters

SOT-143

RATINGS	SYMBOL	CH402H-40PT			UNITS
		MIN.	TYP.	MAX.	
Maximum Recurrent Peak Reverse Voltage	V_{RRM}	-	-	40	Volts
Maximum Average Forward Rectified Current	I_O	-	-	20	mAmps
Total Power Dissipation, T_S< 85 °C	P_{TOT}	-	-	100	mW
Typical Series Inductance	L_S	-	2.0	-	nH
Typical Case Capacitance	C_C	-	0.1	-	pF
Typical Junction Capacitance between Terminal (Note 1)	C_J	-	0.35	0.6	pF
Typical Differential Resistance (Note 2)	R_D	-	225	-	kΩ
Operating and Storage Temperature Range	T_J,T_{STG}	-55	-	+150	°C

ELECTRICAL CHARACTERISTICS (At T_A = 25°C unless otherwise noted)

CHARACTERISTICS	SYMBOL	CH402H-40PT			UNITS
		MIN.	TYP.	MAX.	
Maximum Instantaneous Forward Voltage at I_F= 2mA	V_F	-	0.58	1.00	Volts
Maximum Average Reverse Current at V_R= 40V	I_R	-	-	10	uAmps

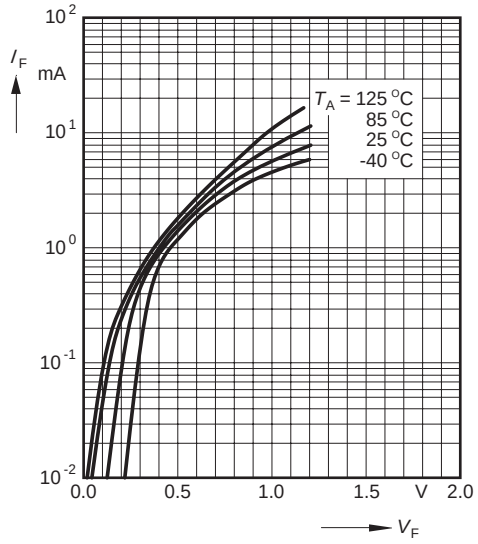
NOTES : 1. Measured at 1.0 MHz and applied reverse voltage of 0 volt.
2. Measured at 10 KHz and applied reverse voltage of 0 volt.
2. ESD sensitive product handling required.

2002-6

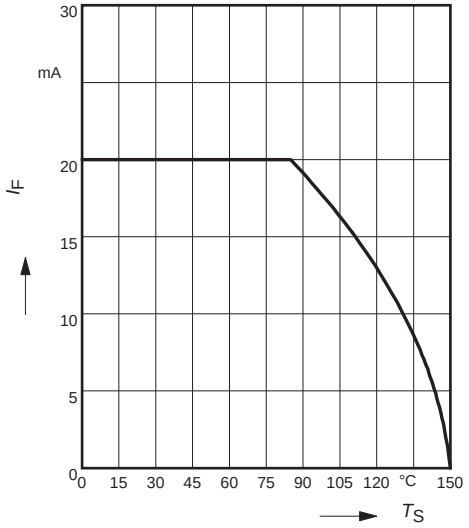
RATING CHARACTERISTIC CURVES (CH402H-40PT)

Forward current $I_F = f(V_F)$

T_A = Parameter

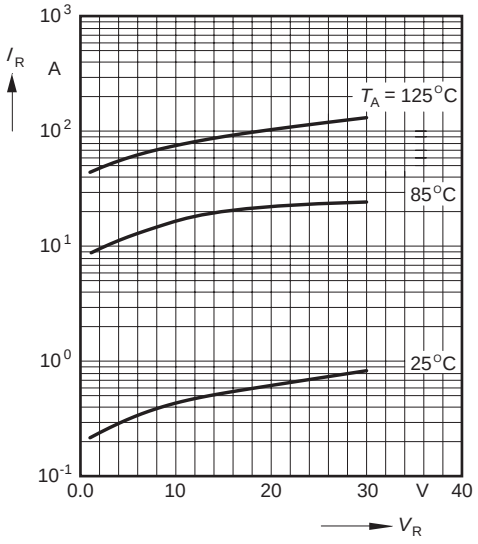


Forward current $I_F = f(T_S)$



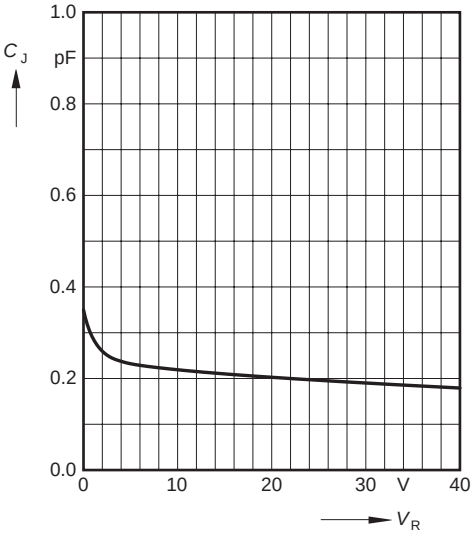
Reverse current $I_R = f(V_R)$

T_A = Parameter



Diode capacitance $C_J = f(V_R)$

f = 1MHz



RATING CHARACTERISTIC CURVES (CH402H-40PT)

Rectifier voltage $V_O = f(V_i)$

f = 900MHz